H CastÃ¡n

List of Publications by Year
in descending order

168	1,427	430874 18	454955 30
papers	citations	h-index	g-index

169	169	169	1326
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Structure and Electrical Behavior of Hafnium-Praseodymium Oxide Thin Films Grown by Atomic Layer Deposition. Materials, 2022, 15, 877.	2.9	2
2	Effect of Dielectric Thickness on Resistive Switching Polarity in TiN/Ti/HfO2/Pt Stacks. Electronics (Switzerland), 2022, 11, 479.	3.1	6
3	Study of TiN/Ti/HfO2/W resistive switching devices: characterization and modeling of the set and reset transitions using an external capacitor discharge. Solid-State Electronics, 2022, , 108385.	1.4	0
4	Empirical Characterization of ReRAM Devices Using Memory Maps and a Dynamic Route Map. Electronics (Switzerland), 2022, 11, 1672.	3.1	1
5	An experimental and simulation study of the role of thermal effects on variability in TiN/Ti/HfO2/W resistive switching nonlinear devices. Chaos, Solitons and Fractals, 2022, 160, 112247.	5.1	7
6	Atomic layer deposited nanolaminates of zirconium oxide and manganese oxide from manganese(III)acetylacetonate and ozone. Nanotechnology, 2021, 32, 335703.	2.6	2
7	Performance Assessment of Amorphous HfO2-Based RRAM Devices for Neuromorphic Applications. ECS Transactions, 2021, 102, 29-35.	0.5	2
8	Hafnium Oxide/Graphene/Hafnium Oxide-Stacked Nanostructures as Resistive Switching Media. ACS Applied Nano Materials, 2021, 4, 5152-5163.	5.0	12
9	Performance Assessment of Amorphous HfO2-Based RRAM Devices for Neuromorphic Applications. ECS Meeting Abstracts, 2021, MA2021-01, 995-995.	0.0	0
10	Thermoelectrical Characterization of Piezoelectric Diaphragms: Towards a Better Understanding of Ferroelectrics for Future Memory Applications. ECS Transactions, 2021, 102, 45-59.	0.5	0
11	Thermoelectrical Characterization of Piezoelectric Diaphragms: Towards a Better Understanding of Ferroelectrics for Future Memory Applications. ECS Meeting Abstracts, 2021, MA2021-01, 1025-1025.	0.0	0
12	Performance Assessment of Amorphous HfO2-Based RRAM Devices for Neuromorphic Applications. ECS Journal of Solid State Science and Technology, 2021, 10, 083002.	1.8	2
13	Effective control of filament efficiency by means of spacer HfAlOx layers and growth temperature in HfO2 based ReRAM devices. Solid-State Electronics, 2021, 183, 108085.	1.4	5
14	Study of the set and reset transitions in HfO2-based ReRAM devices using a capacitor discharge. Solid-State Electronics, 2021, 183, 108113.	1.4	6
15	Analysis of the performance of Nb2O5-doped SiO2-based MIM devices for memory and neural computation applications. Solid-State Electronics, 2021, 186, 108114.	1.4	4
16	Influences of the Temperature on the Electrical Properties of HfO2-Based Resistive Switching Devices. Electronics (Switzerland), 2021, 10, 2816.	3.1	9
17	Double Swing Quiescent-Current: An Experimental Detection Method of Ferroelectricity in Very Leaky Dielectric Films. ECS Transactions, 2020, 97, 3-6.	0.5	1
18	(Invited) Current and Voltage Control of Intermediate States in Bipolar Rram Devices for Neuristor Applications. ECS Transactions, 2020, 97, 17-20.	0.5	1

#	Article	IF	Citations
19	Magnetic properties and resistive switching in mixture films and nanolaminates consisting of iron and silicon oxides grown by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	7
20	Programming Pulse Width Assessment for Reliable and Low-Energy Endurance Performance in Al:HfO2-Based RRAM Arrays. Electronics (Switzerland), 2020, 9, 864.	3.1	25
21	Silicon oxide-niobium oxide mixture films and nanolaminates grown by atomic layer deposition from niobium pentaethoxide and hexakis(ethylamino) disilane. Nanotechnology, 2020, 31, 195713.	2.6	5
22	Using current pulses to control the intermediate conductance states in hafnium oxide-based RRAM devices. , 2020, , .		0
23	Single and complex devices on three topological configurations of HfO2 based RRAM. , 2020, , .		2
24	Structure and behavior of ZrO2-graphene-ZrO2 stacks. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 063411.	2.1	4
25	(Invited) Current and Voltage Control of Intermediate States in Bipolar Rram Devices for Neuristor Applications. ECS Meeting Abstracts, 2020, MA2020-01, 1025-1025.	0.0	0
26	Double Swing Quiescent-Current: An Experimental Detection Method of Ferroelectricity in Very Leaky Dielectric Films. ECS Meeting Abstracts, 2020, MA2020-01, 1016-1016.	0.0	0
27	Control of the set and reset voltage polarity in anti-series and anti-parallel resistive switching structures. Microelectronic Engineering, 2019, 216, 111083.	2.4	3
28	Dynamics of set and reset processes on resistive switching memories. Microelectronic Engineering, 2019, 216, 111032.	2.4	6
29	Controlling the intermediate conductance states in RRAM devices for synaptic applications. Microelectronic Engineering, 2019, 215, 110984.	2.4	14
30	Electrical and magnetic properties of atomic layer deposited cobalt oxide and zirconium oxide nanolaminates. Thin Solid Films, 2019, 669, 294-300.	1.8	8
31	Electrical Characterization of Defects Created by Î³-Radiation in HfO2-Based MIS Structures for RRAM Applications. Journal of Electronic Materials, 2018, 47, 5013-5018.	2.2	9
32	The Role of Defects in the Resistive Switching Behavior of Ta2O5-TiO2-Based Metalâ€“Insulatorâ€“Metal (MIM) Devices for Memory Applications. Journal of Electronic Materials, 2018, 47, 4938-4943.	2.2	2
33	Atomic Layer Deposition of Zirconium Dioxide from Zirconium Tetraiodide and Ozone. ECS Journal of Solid State Science and Technology, 2018, 7, P1-P8.	1.8	4
34	Energy Levels of Defects Created in Silicon Supersaturated with Transition Metals. Journal of Electronic Materials, 2018, 47, 4993-4997.	2.2	2
35	Resistive Switching Properties of Atomic Layer Deposited ZrO<inf>2</inf>-HfO<inf>2</inf> Thin Films. , 2018, , .		2
36	Analysis and control of the intermediate memory states of RRAM devices by means of admittance parameters. Journal of Applied Physics, 2018, 124, .	2.5	15

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37	Atomic Layer Deposition and Properties of HfO₂-Al₂O₃ Nanolaminates. ECS Journal of Solid State Science and Technology, 2018, 7, P501-P508.	1.8	12
38	Electric and Magnetic Properties of Atomic Layer Deposited ZrO₂-HfO₂Thin Films. ECS Journal of Solid State Science and Technology, 2018, 7, N117-N122.	1.8	11
39	Study of the Influence of the Dielectric Composition of Al/Ti/ZrO2:Al2O3/TiN/Si/Al Structures on the Resistive Switching Behavior for Memory Applications. ECS Transactions, 2018, 85, 143-148.	0.5	3
40	Atomic Layer Deposition and Performance of ZrO₂-Al₂O₃Thin Films. ECS Journal of Solid State Science and Technology, 2018, 7, P287-P294.	1.8	8
41	Atomic layer deposition and properties of ZrO2/Fe2O3 thin films. Beilstein Journal of Nanotechnology, 2018, 9, 119-128.	2.8	15
42	Memory Maps: Reading RRAM Devices without Power Consumption. ECS Transactions, 2018, 85, 201-205.	0.5	11
43	Properties of Atomic Layer Deposited Nanolaminates of Zirconium and Cobalt Oxides. ECS Journal of Solid State Science and Technology, 2018, 7, P402-P409.	1.8	0
44	A physically based model for resistive memories including a detailed temperature and variability description. Microelectronic Engineering, 2017, 178, 26-29.	2.4	29
45	Study of the admittance hysteresis cycles in TiN/Ti/HfO2/W-based RRAM devices. Microelectronic Engineering, 2017, 178, 30-33.	2.4	13
46	A physically based model to describe resistive switching in different RRAM technologies. , 2017, , .		0
47	Experimental Observation of Negative Susceptance in HfO₂-Based RRAM Devices. IEEE Electron Device Letters, 2017, 38, 1216-1219.	3.9	10
48	Properties of Zirconium Oxide and Cobalt Ferrite Layered Nanocomposite. ECS Journal of Solid State Science and Technology, 2017, 6, P886-P892.	1.8	2
49	Magnetic and Electrical Performance of Atomic Layer Deposited Iron Erbium Oxide Thin Films. ACS Omega, 2017, 2, 8836-8842.	3.5	3
50	Admittance memory cycles of Ta<inf>2</inf>O<inf>5</inf>-ZrO<inf>2</inf>-based RRAM devices. , 2017, , .		0
51	A Single-Stage uk-based Transformerless Inverter for 1-Ï• Grid-Connected PV Systems. , 2017, , .		3
52	Advanced electrical characterization of atomic layer deposited Al<inf>2</inf>O<inf>3</inf> MIS-based structures. , 2017, , .		0
53	Advances towards 4J lattice-matched including dilute nitride subcell for terrestrial and space applications. , 2016, , .		8
54	(Invited) A Complete Suite of Experimental Techniques for Electrical Characterization of Conventional and Incoming High-k Dielectric-Based Devices. ECS Transactions, 2016, 72, 153-165.	0.5	0

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55	Electrical Properties and Nanoresistive Switching of Ni-HfO2-Si Capacitors. ECS Transactions, 2016, 72, 335-342.	0.5	0
56	Electrical Characterization of Amorphous Silicon MIS-Based Structures for HIT Solar Cell Applications. Nanoscale Research Letters, 2016, 11, 335.	5.7	2
57	Study From Cryogenic to High Temperatures of the High- and Low-Resistance-State Currents of ReRAM Niâ€“HfO₂â€“Si Capacitors. IEEE Transactions on Electron Devices, 2016, 63, 1877-1883.	3.0	15
58	A detailed analysis of the energy levels configuration existing in the band gap of supersaturated silicon with titanium for photovoltaic applications. Journal of Applied Physics, 2015, 118, 245704.	2.5	10
59	Hole trap distribution on 2â€‰MeV electron irradiated high-k dielectrics. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 032201.	1.2	2
60	Atomic Layer Deposition and Characterization of Dysprosiumâ€Doped Zirconium Oxide Thin Films. Chemical Vapor Deposition, 2015, 21, 181-187.	1.3	5
61	Characterization of deep level defects present in mono-like, quasi-mono and multicrystalline silicon solar substrates. Semiconductor Science and Technology, 2015, 30, 035011.	2.0	4
62	Scavenging effect on plasma oxidized Gd2O3grown by high pressure sputtering on Si and InP substrates. Semiconductor Science and Technology, 2015, 30, 035023.	2.0	5
63	Electrical characterization of MIS capacitors based on Dy<inf>2</inf>O<inf>3</inf>-doped ZrO<inf>2</inf> dielectrics. , 2015, , .		0
64	Energy levels distribution in supersaturated silicon with titanium for photovoltaic applications. Applied Physics Letters, 2015, 106, .	3.3	16
65	Charge and current hysteresis in dysprosium-doped zirconium oxide thin films. Microelectronic Engineering, 2015, 147, 55-58.	2.4	3
66	Conduction and stability of holmium titanium oxide thin films grown by atomic layer deposition. Thin Solid Films, 2015, 591, 55-59.	1.8	1
67	Resistive Switching Behavior and Electrical Properties of TiO2:Ho2O3 and HoTiOx Based MIM Capacitors. Materials Research Society Symposia Proceedings, 2014, 1691, 43.	0.1	1
68	Single-parameter model for the post-breakdown conduction characteristics of HoTiOx-based MIM capacitors. Microelectronics Reliability, 2014, 54, 1707-1711.	1.7	0
69	Obtaining fast dissolving disintegrating tablets with different doses of melatonin. International Journal of Pharmaceutics, 2014, 467, 84-89.	5.2	14
70	Electrical study of ScO-based MIS structures using Al and Ti as gate electrodes. , 2013, , .		0
71	Deep level defects on mono-like and polycrystalline silicon solar cells. , 2013, , .		1
72	Experimental verification of intermediate band formation on titanium-implanted silicon. Journal of Applied Physics, 2013, 113, 024104.	2.5	33

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73	2 MeV electron irradiation effects on bulk and interface of atomic layer deposited high-k gate dielectrics on silicon. Thin Solid Films, 2013, 534, 482-487.	1.8	8
74	2 MeV electron irradiation effects on the electrical characteristics of metalâ€“oxideâ€“silicon capacitors with atomic layer deposited Al2O3, HfO2 and nanolaminated dielectrics. Solid-State Electronics, 2013, 79, 65-74.	1.4	23
75	The role of defects in solar cells: Control and detection defects in solar cells. , 2013, , .		7
76	Photocurrent measurements for solar cells characterization. , 2013, , .		0
77	Influence of growth and annealing temperatures on the electrical properties of Nb2O5-based MIM capacitors. Semiconductor Science and Technology, 2013, 28, 055005.	2.0	13
78	Interface quality of Sc2O3 and Gd2O3 films based metalâ€“insulatorâ€“silicon structures using Al, Pt, and Ti gates: Effect of buffer layers and scavenging electrodes. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 01A106.	1.2	5
79	Electrical characterization of atomic-layer-deposited hafnium oxide films from hafnium tetrakis(dimethylamide) and water/ozone: Effects of growth temperature, oxygen source, and postdeposition annealing. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	25
80	Electrical properties of intermediate band (IB) silicon solar cells obtained by titanium ion implantation. AIP Conference Proceedings, 2012, , .	0.4	2
81	Electrical Characterization of High-K Dielectric Gates for Microelectronic Devices. , 2012, , .		1
82	A study of tunneling assisted charge exchange on the inner interface of high-k dielectric stacks. , 2011, , .		0
83	Characterization of SrTiO<inf>3</inf>-based MIM capacitors grown by using different precursors and growth temperatures. , 2011, , .		0
84	Negative-resistance effect in Al<inf>2</inf>O<inf>3</inf> based and nanolaminated MIS structures. , 2011, , .		0
85	Electrical characterization of high-pressure reactive sputtered ScOx films on silicon. Thin Solid Films, 2011, 519, 2268-2272.	1.8	2
86	Electrical characteristics of metal-insulator-semiconductor structures with atomic layer deposited Al2O3, HfO2, and nanolaminates on different silicon substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01AA07.	1.2	41
87	Influence of precursor chemistry and growth temperature on the electrical properties of SrTiO3-based metal-insulator-metal capacitors grown by atomic layer deposition. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01AC04.	1.2	7
88	Electrical characterization of high-k based metal-insulator-semiconductor structures with negative resistance effect when using Al2O3 and nanolaminated films deposited on p-Si. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01A901.	1.2	14
89	Electron Irradiation Effects on Atomic Layer Deposited High-k Gate Dielectrics. ECS Transactions, 2011, 41, 349-359.	0.5	0
90	Effect of interlayer trapping and detrapping on the determination of interface state densities on high-k dielectric stacks. Journal of Applied Physics, 2010, 107, .	2.5	24

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91	Electrical Characterization of High-Pressure Reactive Sputtered Sc₂O₃ Films on Silicon. ECS Transactions, 2010, 28, 287-297.	0.5	1
92	Irradiation effect on dielectric properties of hafnium and gadolinium oxide gate dielectrics. Journal of Vacuum Science & Technology B, 2009, 27, 416.	1.3	18
93	Electrical properties of thin zirconium and hafnium oxide high-k gate dielectrics grown by atomic layer deposition from cyclopentadienyl and ozone precursors. Journal of Vacuum Science & Technology B, 2009, 27, 389.	1.3	18
94	Comparison between the electrical properties of atomic layer deposited thin ZrO2 films processed from cyclopentadienyl precursors. Microelectronic Engineering, 2009, 86, 1689-1691.	2.4	9
95	Electrical characterization of high-k based MIS capacitors using flat-band voltage transients. , 2009, , .		0
96	Study of Atomic Layer Deposited Zirconium Oxide Thin Films by Using Mono-Cyclopentadienyl Based Precursors. , 2009, , .		0
97	Effect of interlayer trapping and detrapping on the determination of interface state densities on high-k dielectric stacks. , 2009, , .		0
98	Electrical characterization of ZrO₂-based MIS structures with highly doped Si substrates. , 2009, , .		0
99	Identification of spatial localization and energetic position of electrically active defects in amorphous high-k dielectrics for advanced devices. Journal of Non-Crystalline Solids, 2008, 354, 393-398.	3.1	7
100	Selection of post-growth treatment parameters for atomic layer deposition of structurally disordered TiO2 thin films. Journal of Non-Crystalline Solids, 2008, 354, 404-408.	3.1	5
101	Influence of interlayer trapping and detrapping mechanisms on the electrical characterization of hafnium oxide/silicon nitride stacks on silicon. Journal of Applied Physics, 2008, 104, .	2.5	25
102	Comparative Study of Flatband Voltage Transients on High-k Dielectric-Based Metalâ€“Insulatorâ€“Semiconductor Capacitors. Journal of the Electrochemical Society, 2008, 155, G241.	2.9	9
103	Electrical properties of high-pressure reactive sputtered thin hafnium oxide high-kgate dielectrics. Semiconductor Science and Technology, 2007, 22, 1344-1351.	2.0	16
104	Electrical Characterization of High-k Dielectrics by Means of Flat-Band Voltage Transient Recording. Materials Research Society Symposia Proceedings, 2007, 996, 1.	0.1	0
105	Electrical Properties of Atomic-Layer-Deposited Thin Gadolinium Oxide High-k Gate Dielectrics. Journal of the Electrochemical Society, 2007, 154, G207.	2.9	36
106	Experimental observations of temperature-dependent flat band voltage transients on high-k dielectrics. Microelectronics Reliability, 2007, 47, 653-656.	1.7	17
107	Influence of single and double deposition temperatures on the interface quality of atomic layer deposited Al2O3 dielectric thin films on silicon. Journal of Applied Physics, 2006, 99, 054902.	2.5	47
108	Experimental investigation of the electrical properties of atomic layer deposited hafnium-rich silicate films on n-type silicon. Journal of Applied Physics, 2006, 100, 094107.	2.5	10

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109	DISORDERED STRUCTURE AND DENSITY OF GAP STATES IN HIGH-PERMITTIVITY THIN SOLID FILMS. , 2006, , 123-134.		1
110	ELECTRICAL DEFECTS IN ATOMIC LAYER DEPOSITED HFO2 FILMS ON SILICON: INFLUENCE OF PRECURSOR CHEMISTRIES AND SUBSTRATE TREATMENT. , 2006, , 287-298.		0
111	On the influence of substrate cleaning method and rapid thermal annealing conditions on the electrical characteristics of Al/SiNx/SiO2/Si fabricated by ECR-CVD. Microelectronics Reliability, 2005, 45, 978-981.	1.7	1
112	Electrical characterization of hafnium oxide and hafnium-rich silicate films grown by atomic layer deposition. Microelectronics Reliability, 2005, 45, 949-952.	1.7	7
113	Comparative study on electrical properties of atomic layer deposited high-permittivity materials on silicon substrates. Thin Solid Films, 2005, 474, 222-229.	1.8	13
114	A comparative study of atomic layer deposited advanced high-k dielectrics. , 2005, , .		0
115	A comparative study of the electrical properties of TiO2films grown by high-pressure reactive sputtering and atomic layer deposition. Semiconductor Science and Technology, 2005, 20, 1044-1051.	2.0	79
116	Conductance Transient Comparative Analysis of Electron-Cyclotron Resonance Plasma-Enhanced Chemical Vapor Deposited SiNx, SiO2/SiNxand SiOxNyDielectric Films on Silicon Substrates. Japanese Journal of Applied Physics, 2004, 43, 66-70.	1.5	1
117	Effect of growth temperature and postmetallization annealing on the interface and dielectric quality of atomic layer deposited HfO2 on p and n silicon. Journal of Applied Physics, 2004, 96, 1365-1372.	2.5	13
118	The electrical-interface quality of as-grown atomic-layer-deposited disordered HfO2 on p- and n-type silicon. Semiconductor Science and Technology, 2004, 19, 1141-1148.	2.0	31
119	Title is missing!. Journal of Materials Science: Materials in Electronics, 2003, 14, 287-290.	2.2	1
120	A comparative study of anodic tantalum pentoxide and high-pressure sputtered titanium oxide. Journal of Materials Science: Materials in Electronics, 2003, 14, 375-378.	2.2	2
121	Conductance transient, capacitanceâ€“voltage and deep-level transient spectroscopy characterization of atomic layer deposited hafnium and zirconium oxide thin films. Solid-State Electronics, 2003, 47, 1623-1629.	1.4	21
122	On the interface quality of MIS structures fabricated from Atomic Layer Deposition of HfO2, Ta2O5 and Nb2O5â^'Ta2O5â^'Nb2O5 dielectric thin films. Materials Research Society Symposia Proceedings, 2003, 786, 3181.	0.1	0
123	Conductance transient comparative analysis of ECR-PECVD deposited SiNx, SiO2/SiNx and SiOxNy dielectric films on silicon substrates. Materials Research Society Symposia Proceedings, 2003, 786, 3121.	0.1	0
124	Interfacial State Density and Conductance-Transient Three-Dimensional Profiling of Disordered-Induced Gap States on Metal Insulator Semiconductor Capacitors Fabricated from Electron-Cyclotron Resonance Plasma-Enhanced Chemical Vapor Deposited SiOxNyHzFilms. Japanese Journal of Applied Physics, 2003, 42, 4978-4981.	1.5	4
125	Experimental Verification of Direct Tunneling Assisted Electron Capture of Disordered-Induced Gap States in Metal-Insulator-Semiconductor Structures. Japanese Journal of Applied Physics, 2002, 41, L1215-L1217.	1.5	6
126	Conductance-transient three-dimensional profiling of disordered induced gap states on metal-insulator-semiconductor structures. Materials Research Society Symposia Proceedings, 2001, 699, 441.	0.1	0

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127	Radio-Frequency Impedance Analysis of Anodic Tantalum Pentoxide Thin Films. Materials Research Society Symposia Proceedings, 2001, 699, 651.	0.1	0
128	Tantalum pentoxide obtained from TaNx and TaSi2 anodisation: an inexpensive and thermally stable high k dielectric. Solid-State Electronics, 2001, 45, 1441-1450.	1.4	9
129	Title is missing!. Journal of Materials Science: Materials in Electronics, 2001, 12, 263-267.	2.2	4
130	DLTS and conductance transient investigation on defects in anodic tantalum pentoxide thin films. Journal of Materials Science: Materials in Electronics, 2001, 12, 317-321.	2.2	2
131	Influence of electron cyclotron resonance nitrogen plasma exposure on the electrical characteristics of SiN[sub x]:H/InP structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 186.	1.6	10
132	Electrical Characterization of Al/SiNx:H/n and p-In0.53Ga0.47As Structures by Deep-Level Transient Spectroscopy and Conductance Transient Techniques. Japanese Journal of Applied Physics, 2001, 40, 4479-4484.	1.5	7
133	Electrical characteristics of anodic tantalum pentoxide thin films under thermal stress. Microelectronics Reliability, 2000, 40, 659-662.	1.7	9
134	Interface quality study of ECR-deposited and rapid thermal annealed silicon nitride Al/SiNx:H/InP and Al/SiNx:H/In0.53Ga0.47As structures by DLTS and conductance transient techniques. Microelectronics Reliability, 2000, 40, 845-848.	1.7	26
135	Electrical Characterization of Low Nitrogen Content Plasma Deposited and Rapid Thermal Annealed Al/SiNx:H/InP Metal-Insulator-Semiconductor Structures. Japanese Journal of Applied Physics, 2000, 39, 6212-6215.	1.5	6
136	Thermally induced improvements on SiNx:H/InP devices. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 2178-2182.	2.1	12
137	Electrical characterization of He-ion implantation-induced deep levels in p+n InP junctions. Journal of Applied Physics, 1999, 86, 4855-4860.	2.5	0
138	Electrical characterization of a He ion implantation-induced deep level existing in p+n InP junctions. Journal of Applied Physics, 1999, 85, 7978-7980.	2.5	1
139	Electrical characterization of electron cyclotron resonance deposited silicon nitride dual layer for enhanced Al/SiNx:H/InP metalâ€“insulatorâ€“semiconductor structures fabrication. Journal of Applied Physics, 1999, 86, 6924-6930.	2.5	7
140	Use of anodic tantalum pentoxide for high-density capacitor fabrication. Journal of Materials Science: Materials in Electronics, 1999, 10, 379-384.	2.2	17
141	Title is missing!. Journal of Materials Science: Materials in Electronics, 1999, 10, 413-418.	2.2	0
142	Title is missing!. Journal of Materials Science: Materials in Electronics, 1999, 10, 373-377.	2.2	3
143	Fabrication of Ta₂O₅ Thin Films by Anodic Oxidation of Tantalum Nitride and Tantalum Silicide: Growing Mechanisms, Electrical Characterization and ULSI M-I-M Capacitor Performances. Materials Research Society Symposia Proceedings, 1999, 567, 371.	0.1	5
144	Deposition of SiNx:H thin films by the electron cyclotron resonance and its application to Al/SiNx:H/Si structures. Journal of Applied Physics, 1998, 83, 332-338.	2.5	48

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145	Electrical characterization of deep levels existing in Mg-Si- and Mg-P-Si-implanted n InP junctions. Semiconductor Science and Technology, 1998, 13, 389-393.	2.0	2
146	Good quality Al/SiNx:H/InP metal-insulator-semiconductor devices obtained with electron cyclotron resonance plasma method. Journal of Applied Physics, 1998, 83, 600-603.	2.5	15
147	Detailed electrical characterization ofDXcenters in Se-doped AlxGa1â^'xAs. Journal of Applied Physics, 1997, 82, 4338-4345.	2.5	6
148	Deep levels in p+-n junctions fabricated by rapid thermal annealing of Mg or Mg/P implanted InP. Journal of Applied Physics, 1997, 81, 3143-3150.	2.5	5
149	Experimental observation of conductance transients in Al/SiNx:H/Si metal-insulator-semiconductor structures. Applied Physics Letters, 1997, 71, 826-828.	3.3	45
150	Conductance Transients Study of Slow Traps in Al/SiNx:H/Si and Al/SiNx:H/InP Metal-Insulator-Semiconductor Structures. Materials Research Society Symposia Proceedings, 1997, 500, 87.	0.1	0
151	Thermal emission processes of DX centres in AlxGa1â^'xAs:Si. Solid-State Electronics, 1997, 41, 103-109.	1.4	1
152	Dopant level freezeâ€out and nonideal effects in 6Hâ€“SiC epilayer junctions. Journal of Applied Physics, 1996, 79, 310-315.	2.5	3
153	Ability of capacitanceâ€“voltage transient technique to study spatial distribution and electric field dependence of emission properties of deep levels in semiconductors. Materials Science and Technology, 1995, 11, 1074-1078.	1.6	2
154	Deepâ€level transient spectroscopy and electrical characterization of ionâ€implantedpâ€njunctions into undoped InP. Journal of Applied Physics, 1995, 78, 5325-5330.	2.5	10
155	Characterization of the damage induced in boron-implanted and RTA annealed silicon by the capacitance-voltage transient technique. Semiconductor Science and Technology, 1994, 9, 1637-1648.	2.0	17
156	Electrical characterization of MOS structures fabricated on SF6 and SF6 + C2ClF5 reactive ion etched silicon. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 1362-1366.	1.4	0
157	Influence of refilling effects on deepâ€level transient spectroscopy measurements in Seâ€doped AlxGa1â^'xAs. Journal of Applied Physics, 1992, 72, 525-530.	2.5	10
158	A study of metalâ€oxideâ€semiconductor capacitors fabricated on SF6and SF6+Cl2reactiveâ€ionâ€etched Si. Journal of Applied Physics, 1992, 71, 2710-2716.	2.5	7
159	Admittance spectroscopy in junctions. Solid-State Electronics, 1992, 35, 285-297.	1.4	74
160	Characterization of the DX centers in AlGaAs:Si by admittance spectroscopy. Journal of Applied Physics, 1991, 69, 4300-4305.	2.5	16
161	Rie-induced damage in MOS structures. Solid-State Electronics, 1990, 33, 1419-1423.	1.4	3
162	Interface state density measurement in MOS structures by analysis of the thermally stimulated conductance. Solid-State Electronics, 1990, 33, 987-992.	1.4	13

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163	Characterization of the EL2 center in GaAs by optical admittance spectroscopy. Journal of Applied Physics, 1990, 67, 6309-6314.	2.5	6
164	Constant-capacitance deep-level optical spectroscopy. Solid-State Electronics, 1989, 32, 287-293.	1.4	4
165	Optical admittance spectroscopy: A new method for deep level characterization. Journal of Applied Physics, 1987, 61, 2541-2545.	2.5	29
166	Electron thermal emission rates of nickel centers in silicon. Solid-State Electronics, 1986, 29, 883-884.	1.4	13
167	Electrical characterization of atomic-layer-deposited hafnium silicate for alternative gate dielectric application. , 0, , .		2
168	Interface quality of high-pressure reactive sputtered and atomic layer deposited titanium oxide thin films on silicon. , 0, , .		0